

## Silicon Standard Recovery Diode

 $V_{RRM} = 50 \text{ V} - 1000 \text{ V}$ 
 $I_F = 35 \text{ A}$ 

### Features

- High Surge Capability
- Types up to 1000 V  $V_{RRM}$

**DO-5 Package**


### Maximum ratings, at $T_j = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N1183 (R)	1N1184 (R)	1N1186 (R)	1N1187 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		50	100	200	300	V
RMS reverse voltage	$V_{RMS}$		35	70	140	210	V
DC blocking voltage	$V_{DC}$		50	100	200	300	V
Continuous forward current	$I_F$	$T_C \leq 140 \text{ }^\circ\text{C}$	35	35	35	35	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}$ , $t_p = 8.3 \text{ ms}$	595	595	595	595	A
Operating temperature	$T_j$		-65 to 190	-65 to 190	-65 to 190	-65 to 190	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N1183 (R)	1N1184 (R)	1N1186 (R)	1N1187 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 35 \text{ A}$ , $T_j = 25 \text{ }^\circ\text{C}$	1.2	1.2	1.2	1.2	V
Reverse current	$I_R$	$V_R = 50 \text{ V}$ , $T_j = 25 \text{ }^\circ\text{C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 50 \text{ V}$ , $T_j = 140 \text{ }^\circ\text{C}$	10	10	10	10	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.25	0.25	0.25	0.25	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

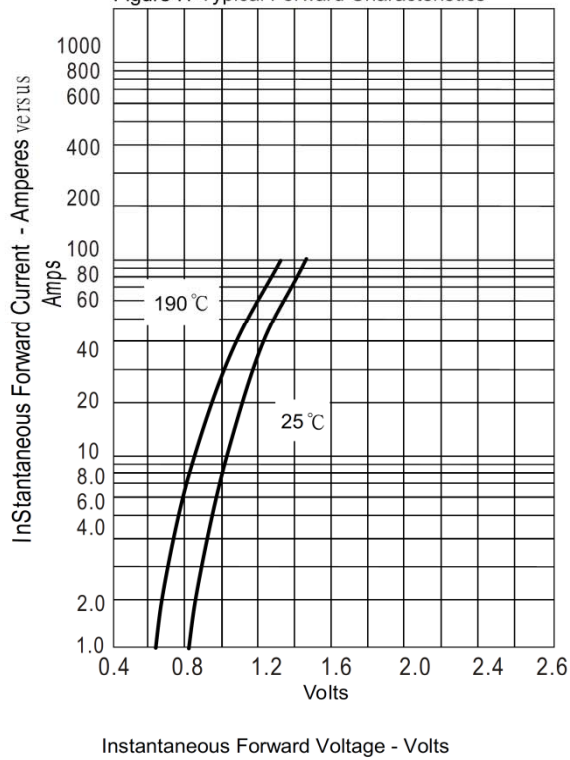


Figure .2-Forward Derating Curve

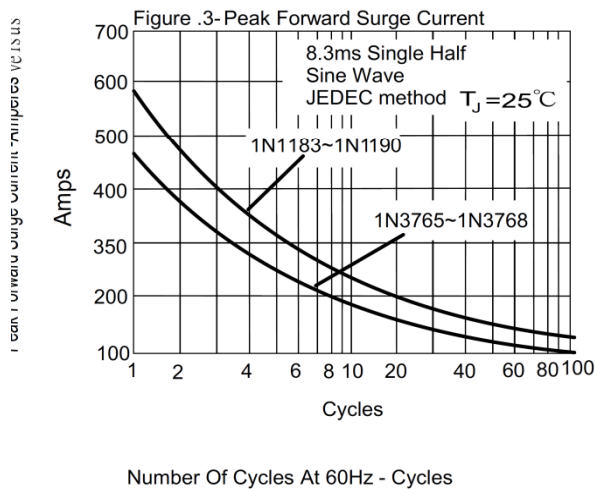
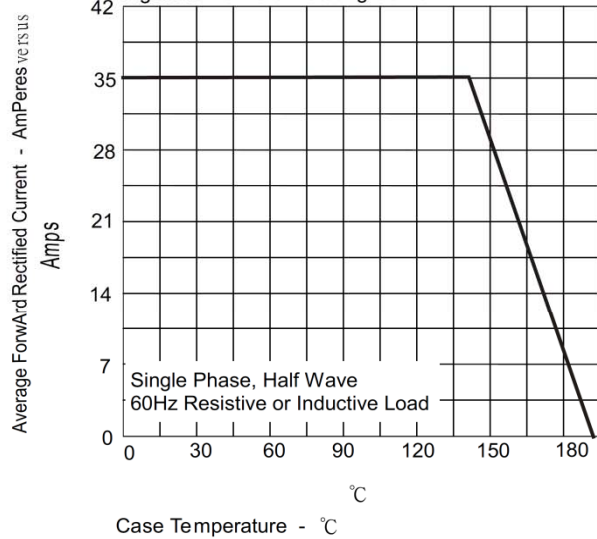


Figure .4-Typical Reverse Characteristics

